



FEATURES

- High bandwidth
- X-cut for high stability
- Low drive voltage
- Low insertion loss

APPLICATIONS

- Digital communications
- General purpose intensity modulation
- Test and measurement

OPTIONS

- High extinction ratio versions
- 2000 nm, 1300 nm, 1060 nm, 850 nm

RELATED EQUIPMENTS

- RF amplifiers
- MBC-DG Automatic Bias Controllers
- ModBox-CBand-NRZ
- ModBox-CBand-PAM4
- ModBox-VNA-CBand

The MX-LN series are lithium niobate (LiNbO₃) intensity modulators designed for optical communications at data rates up to 44 Gb/s.

The X-cut design of these Mach-Zehnder modulators confer them an unmatched stability in a wide range of operational conditions, as well as a zero chirp performance. IXblue proprietary waveguide design offers a low insertion loss combined with a high contrast. The MX-LN series are ideally suited for 10 Gb/s up to 44 Gb/s optical transmission with NRZ, RZ, DPSK, Duo Binary modulation formats and are key device for a large variety of high bandwidth applications.

MX-LN-10 Performance Highlights

Parameter	Min	Typ	Max	Unit
Operating wavelength	1530	-	1625	nm
Insertion loss	-	3.5	-	dB
Insertion loss (with low IL option)	-	2.7	3	dB
Electro-optical bandwidth	10	12	-	GHz

Specifications given at 25 °C, 1550 nm

MX-LN-20 Performance Highlights

Parameter	Min	Typ	Max	Unit
Operating wavelength	1530	-	1625	nm
Insertion loss	-	3.5	-	dB
Electro-optical bandwidth	20	25	-	GHz
V _π RF @50 kHz	-	5	-	V

Specifications given at 25 °C, 1550 nm

MX-LN-40 Performance Highlights

Parameter	Min	Typ	Max	Unit
Operating wavelength	1530	-	1625	nm
Insertion loss	-	3.5	-	dB
Electro-optical bandwidth	28	30	-	GHz
V _π RF @50 kHz	-	5	-	V

Specifications given at 25 °C, 1550 nm

MX-LN-10

10 GHz Intensity modulator

Electrical Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optic bandwidth	S_{21}	RF electrodes, from 2 GHz	10	12	-	GHz
Ripple S_{21}	ΔS_{21}	RF electrodes, $f < 12$ GHz	-	0.5	1	dB
Electrical return loss	S_{11}	RF electrodes	-	-12	-10	dB
V_{π} RF @50 kHz	$V_{\pi RF_{50\text{ kHz}}}$	RF electrodes, @1550 nm	-	5.5	6.5	V
V_{π} RF @10 Gb/s PRBS	$V_{\pi RF_{10\text{ Gb/s}}}$	RF electrodes, @1550 nm	-	6.5	7	V
V_{π} DC electrodes	$V_{\pi DC}$	DC electrodes	-	6.5	7	V
RF input impedance	Z_{in-RF}	-	-	50	-	Ω
DC input impedance	Z_{in-DC}	-	-	1	-	M Ω

50 Ω RF input

Optical Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-	Lithium Niobate X-Cut Y-Prop			
Operating wavelength	λ	-	1530	1550	1625	nm
Insertion loss	IL	Without connectors	-	3.5	-	dB
Insertion loss (with low IL option)	LIL	Without connectors	-	2.7	3	dB
DC extinction ratio	ER	Measured with narrow source linewidth < 200 MHz	20	22	-	dB
Optical return loss	ORL	-	-40	-45	-	dB
Chirp	α	-	-0.1	0	0.1	-

All specifications given at 25°C, 1550 nm, unless differently specified

Absolute Maximum Ratings

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. These are absolute stress ratings only. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of the data sheet. Exposure to absolute maximum ratings for extended periods can adversely affect device reliability.

Parameter	Symbol	Min	Max	Unit
RF input power	EP_{in}	-	28	dBm
Bias voltage	V_{bias}	-20	+20	V
Optical input power	OP_{in}	-	20	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

MX-LN-20

20 GHz Intensity modulator

Electrical Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optic bandwidth	S_{21}	RF electrodes, from 2 GHz	20	25	-	GHz
Ripple S_{21}	ΔS_{21}	RF electrodes, $f < 20$ GHz	-	0.5	1	dB
Electrical return loss	S_{11}	RF electrodes	-	-12	-10	dB
V_{π} RF @ 50 kHz	$V_{\pi RF_{50\text{ kHz}}}$	RF electrodes, @ 1550 nm	-	5	5.5	V
V_{π} RF @ 20 Gb/s PRBS	$V_{\pi RF_{20\text{ Gb/s}}}$	RF electrodes, @ 1550 nm	-	5.5	6	V
V_{π} DC electrodes	$V_{\pi DC}$	DC electrodes	-	6.5	7	V
RF input impedance	Z_{in-RF}	-	-	50	-	Ω
DC input impedance	Z_{in-DC}	-	-	1	-	M Ω

50 Ω RF input

Optical Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-	Lithium Niobate X-Cut Y-Prop			
Operating wavelength	λ	-	1530	1550	1625	nm
Insertion loss	IL	Without connectors	-	3.5	4.5	dB
DC extinction ratio	ER	Measured with narrow source linewidth < 200 MHz	20	22	-	dB
Optical return loss	ORL	-	-40	-45	-	dB
Chirp	α	-	-0.1	0	0.1	-

All specifications given at 25 °C, 1550 nm, unless different specified

Absolute Maximum Ratings

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Parameter	Symbol	Min	Max	Unit
RF input power	EP_{in}	-	28	dBm
Bias voltage	V_{bias}	-20	+20	V
Optical input power	OP_{in}	-	20	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

MX-LN-40

40 GHz Intensity modulator

Electrical Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optic bandwidth	S_{21}	RF electrodes, from 2 GHz	28	30	-	GHz
Ripple S_{21}	ΔS_{21}	RF electrodes, $f < 30$ GHz	-	0.5	1	dB
Electrical return loss	S_{11}	RF electrodes	-	-12	-10	dB
$V\pi$ RF @ 50 kHz	$V\pi_{RF, 50\text{ kHz}}$	RF electrodes, @ 1550 nm	-	5	6	V
$V\pi$ DC electrodes	$V\pi_{DC}$	DC electrodes, @ 1550 nm	-	6.5	7	V
RF input impedance	Z_{in-RF}	-	-	50	-	Ω
DC input impedance	Z_{in-DC}	-	1	-	-	M Ω

50 Ω RF input

Optical Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-	Lithium Niobate X-Cut Y-Prop			
Operating wavelength	λ	-	1530	1550	1625	nm
Insertion loss	IL	Without connectors	-	3.5	4.5	dB
DC extinction ratio	ER	Measured with narrow source linewidth < 200 MHz	20	22	-	dB
Optical return loss	ORL	-	-40	-45	-	dB
Chirp	α	-	-0.1	0	0.1	-

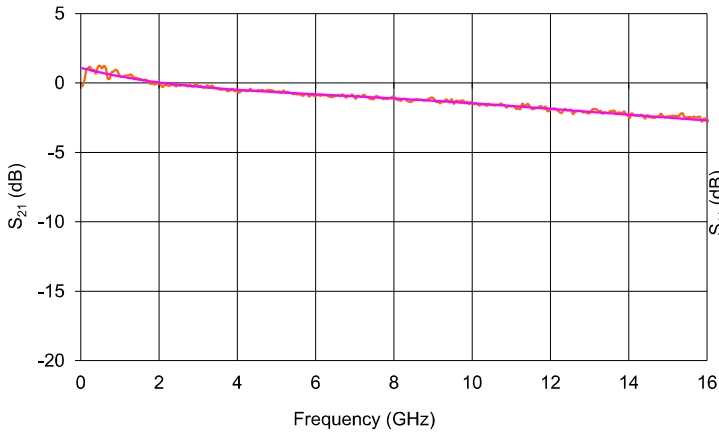
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Absolute Maximum Ratings

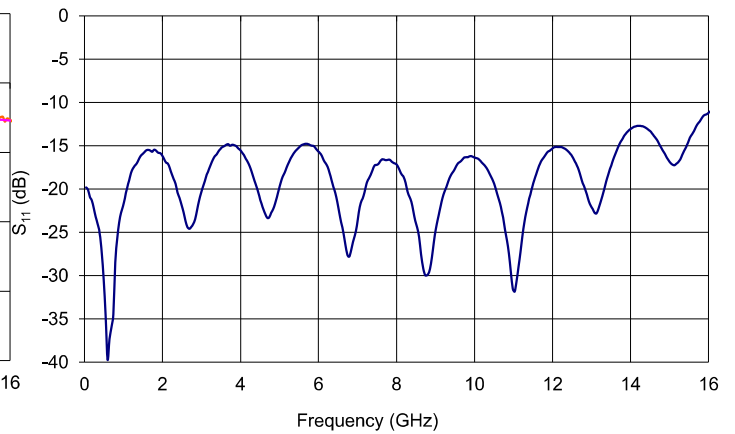
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Parameter	Symbol	Min	Max	Unit
RF input power	EP_{in}	-	28	dBm
Bias voltage	V_{bias}	-20	+20	V
Optical input power	OP_{in}	-	20	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

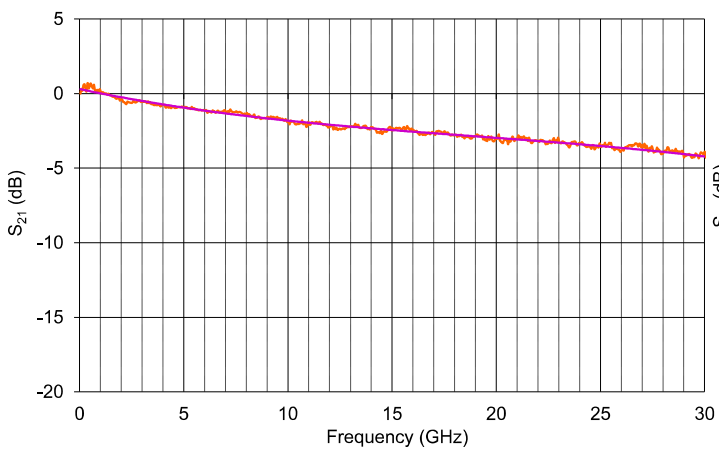
MX-LN-10 Typical S_{21} Curve



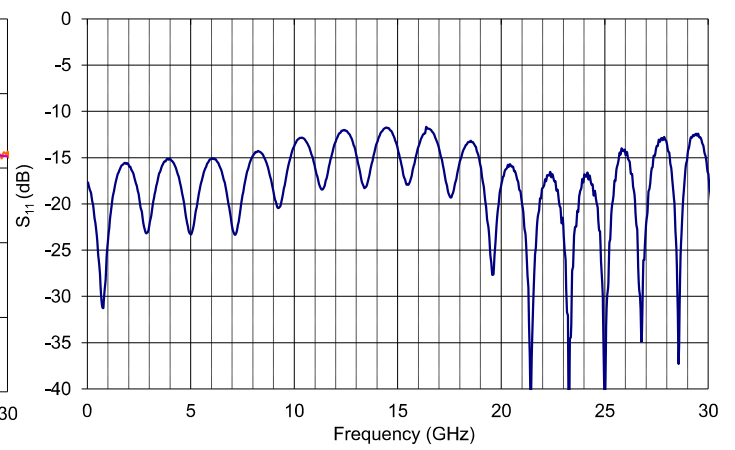
MX-LN-10 Typical S_{11} Curve



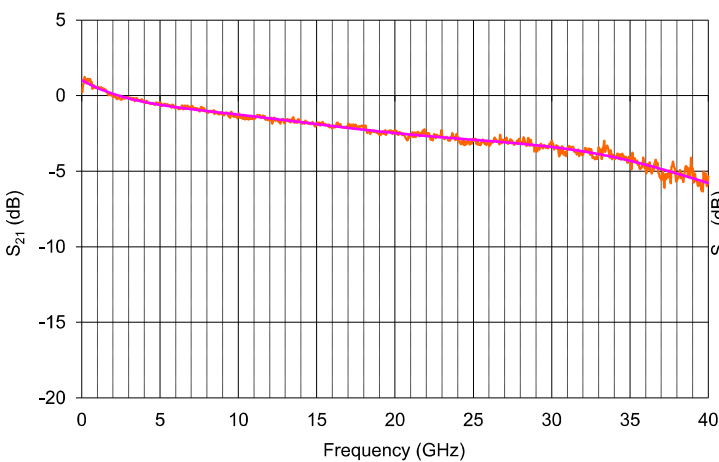
MX-LN-20 Typical S_{21} Curve



MX-LN-20 Typical S_{11} Curve



MX-LN-40 Typical S_{21} Curve



MX-LN-40 Typical S_{11} Curve

